

Amendments to the Claims:

None of the claims have been amended herein. All of the pending claims are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as previously amended.

Listing of Claims:

Claims 1-26 (cancelled).

27. (Previously Presented) A method of establishing electrical contact between a semiconductor substrate and a semiconductor device, comprising:
providing a substrate with an overlying insulating layer;
etching a hole through the insulating layer to the substrate;
introducing doped polycrystalline silicon into the hole;
introducing at least one titanium layer within the hole over the doped polycrystalline silicon;
introducing at least one non-titanium layer over the at least one titanium layer and within the hole;
siliciding the titanium layer;
nitridizing the non-titanium layer by exposing the non-titanium layer to a N_2/NH_3 ambient at a temperature of about $360^{\circ}C$; and
forming the semiconductor device over the non-titanium layer.

Claims 28-72 (Cancelled).

73. (Original) The method of claim 27, further comprising exposing the the non-titanium layer to a N_2/NH_3 ambient under a pressure of approximately 4.5 torr.

74. (Original) The method of claim 27, wherein exposing the non-titanium layer to a N_2/NH_3 ambient comprises exposing a tungsten layer to a N_2/NH_3 ambient.

75. (Original) The method of claim 27, introducing doped polycrystalline silicon into the hole comprises filling the hole with doped polycrystalline silicon and subsequently removing a portion of the doped polycrystalline silicon from the hole.

76. (Original) The method of claim 75, wherein removing a portion of the doped polycrystalline silicon comprises etching the doped polycrystalline silicon.

77. (Original) The method of claim 27, further comprising siliciding the titanium layer prior to introducing at least one non-titanium layer over the at least one titanium layer and within the hole.

78. (Original) The method of claim 27, wherein introducing at least one titanium layer comprises selectively depositing the titanium layer on the polycrystalline silicon through chemical vapor deposition.

79. (Original) The method of claim 27, wherein siliciding the titanium layer comprises exposing the semiconductor substrate to TiCl_4 with a reactive gas and a carrier gas at a temperature about 400°C in a reaction chamber under a pressure of approximately 0.2 to 2 torr while an rf voltage is applied to the reaction chamber.

80. (Original) The method of claim 27, further comprising providing an oxidation barrier between the non-titanium layer and the semiconductor device.